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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM-2 Cont. 4	APPLICATION NO. 10/672,961
	NFORMATION DISCLOSURE	APPLICANT Glenn J. Leedy	CONFIRMATION NO. 9439
	STATEMENT BY APPLICANT	FILING DATE September 26, 2003	GROUP 2811

U.S. PATENT DOCUMENTS

EXAMINE R	NI MBED DA		NAME	CLASS	SUBCLASS	FILING DATE IF
INITIAL	NUMBER					APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	257	419	
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
1.	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
-	4,693,770	09/15/87	Hatada	156	151	

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FORM PTO-1449		OF COMMERCE DEMARK OFFICE	ATTY. DOCKET NO. ELM-2 Cont. 4		APPLICATION NO. 10/672,961		
	DISCLOS	APPLICAN Glenn J. Le		CONFIRMATION NO 9439			
STATEMENT BY APPLICANT				FILING DA		GROUP 2811	
4,702,3	336 10	/27/87	Maeda et al.	180	197		
4,702,9	36 10	/27/87	Seibert et al.	427	583		
4,706,1	166 11	/10/87	Go	361	403		
4,721,9	38 01	/26/88	Stevenson	338	4		
4,761,6	81 08	/02/88	Reid	357	68		
4,784,7		/15/88	Holmen et al.	156	647		
4,810,6		/07/89	Freeman	438	386		
4,825,2	277 04	/25/89	Mattox et al.	257	639		
4,857,4		/15/89	Tam et al.	438	619		
4,924,5	89 05	/15/90	Leedy	438	6		
4,940,9		/10/90	Borel et al.	313	306		
		/26/96	Borel et al.	315	306		
4,950,9		/21/90	Vranish et al.	324	207.23		
4,952,4	46 08	/18/90	Lee et al.	428	220		
4,954,8	65 09	/04/90	Rokos	257	378		
4,957,8	82 09/	/18/90	Shinomiya	438	65		
4,965,4	15 10/	/23/90	Young et al.	200	83 N		
4,966,6	63 10	/30/90	Mauger	205	656		
4,994,7	35 02/	/19/91	Leedy	324	158		
5,008,6	19 04/	/16/91	Keogh et al.	324	207.17		
5,010,0	24 04/	/23/91	Allen et al.	438	659		
5,020,2	19 06/	/04/91	Leedy	29	846		
5,034,6	85 07/	/23/91	Leedy	324	158 F		
5,070,0	26 12/	/03/91	Greenwald et al.	437	3		
5,071,5	10 12/	/10/91	Findler et al.	156	647	-	
5,098,8		/24/92	Machado et al.	438	788		
5,103,5		/14/92	Leedy	29	832		
5,110,3		/05/92	Mauger	148	33.2		
5,111,2		/05/92	Eichelberger	357	75		
5,116,7		/26/92	Chan et al.	438	234		
5,130,8		/14/92	Miller	361	393		
5,132,2		/21/92	Roy	438	477		

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FORM PTO-1449		NT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-2 Cont		APPLICATION NO. 10/672,961	
	FORMATION DISCL		APPLICANT Glenn J. Leedy		CONFIRMATION NO 9439	
	TATEMENT BY APP	LICANT	FILING DAT September 2		GROUP 2811	
						
5,151,	775 09/29/92	2 Hadwin	357	80		
5,156,	909 10/20/92	Henager, Jr. et al.	428	334		
5,203,	731 04/20/93	3 Zimmerman	445	24		
5,225,	771 07/06/93	3 Leedy	324	158		
5,236,	118 08/17/93	Bower et al.	228	193		
5,262,		Bureau et al.	437	183		
5,270,		Bertin et al.	437	209		
5,273,	940 12/28/93	3 Sanders	437	209		
5,274,	270 12/28/93	3 Tuckerman	257	758		
5,279,	865 01/18/94	1 Chebi et al.	427	574		
5,284,		Nakanishi et al.	437	183		
5,323,		1 Leedy	257	48		
5,324,		1 Wojnarowski	437	225		
5,354,		1 Leedy	438	411		
5,363,		4 MacDonald	315	366	·	
5,385,		Nelson et al.	514	291		
5,385,		5 Goossen	156	630		
5,420,		5 Shimoji	257	622		
5,424,			361	735		
5,426,			437	208		
5,426,	··········	5 Akagi et al.	324	239		
5,432,			324	240		
5,432,			365	63		
5,434,			324	67		
5,451,			430	313		
5,453,			437	203		
5,457,			29	895		
5,476,			437	132		
5,489,			437	208		
5,502,			365	51		
5,512,			430	30		
5,527,			430	5		

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FORM PTO-1449		IT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-2 Cont		APPLICATION NO. 10/672,961
	FORMATION DISCLO	APPLICANT Glenn J. Leedy		CONFIRMATION NO 9439	
5	CANT	FILING DAT		GROUP 2811	
5,529,	829 06/25/96	Koskenmaki et al.	428	167	
5,534,		Frye et al.	437	209	
5,555,	 	Toshiaki et al.	365	200	
5,563,		Ramm et al.	437	51	
5,571,		Leedy	437	51	
5,580,		Leedy	430	5	
5,581,		Ludwig et al.	365	63	
5,582,		Pierrat	430	5	
5,583,		Hornbeck	359	291	
5,592,		Leedy	257	347	
5,592,		Leedy	257 619		
5,595,		Heijboer	439	20	
5,606,		Noda	257	226	
5,627,		Tennant et al.	438	113	
5,629,		Leedy	430	313	
5,633,	· · · · · · · · · · · · · · · · · · ·	Leedy	435	228	
5,637,		Val	438	686	
5,654,		Leedy	430	315	
5,654,		Leedy	438	25	
5,656,		Hudak et al.	438	15	
5,675,	····	Chen et al.	257	774	
5,694,		Ohara et al.	395	566	
5,725,		Leedy	430	315	
5,750,		Weise et al.	427	579	
5,760,		Bozso et al.	257	777	
5,773,		Okonogi	428	446	
5,786,		Rolfson	430	5	
5,793,		Zavracky et al.	257	777	
5,831,		Ray	257	48	
5,834,		Leedy	438	107	
5,840,		Leedy	438	6	
5,856,		Ito et al.	257	370	

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FORM PTO-	1449 U.S. DE PATEN			APPLICATIO 10/672,961	APPLICATION NO. 10/672,961						
INFORMATION DISCLOSURE						APPLICANT Glenn J. Leedy		CONFIRMAT 9439	CONFIRMATION NO 9439		
STATEMENT BY APPLICANT						FILING DAT September		GROUP 2811			
		·									
	5,868,949	02/09/	99	Sotokaw	a et al.	216	18				
	5,869,354	02/09/	99	Leedy		438	110				
	5,870,176	02/09/		Sweatt e	t al.	355	53				
	5,880,010	03/09/		Davidsor		438	455				
	5,882,532	03/16/		Field et a		216	2				
	5,902,118	05/11/		Hübner		438	106				
	5,915,167	06/22/		Leedy		438	108				
	5,946,559	08/31/	\rightarrow	Leedy		438	157				
	5,985,693	11/16/	99	Leedy		438	107				
	5,998,069	12/07/	99	Cutter et	al.	430	5				
	6,008,126	12/28/	99	Leedy		438	667				
	6,020,257	02/01/	00 Leedy		438	626					
	6,045,625	04/04/	00	00 Houston		148	33.3				
	6,084,284	07/04/	00	00 Adamic, Jr.		257	506				
	6,097,096	08/01/	00	OO Gardner et al.		257	777				
	6,133,640	10/17/	01 Tayanaka 01 Aleshin et al. 01 Leedy			257	778				
	6,194,245 B1	02/27/			438	57					
	6,197,456 B1	03/06/			et al.	430	5				
	6,208,545 B1	03/27/				365	51				
	6,236,602 B1	05/22/				365	201				
	6,261,728 B1	07/17/	01	01 Lin		430	30				
	6,288,561 B1	09/11/	01	Leedy	Leedy		760				
	6,294,909 B1	09/25/	01)1 Leedy		324	207.17		-		
			FO	REIGN P	ATENT DOCU	MENTS					
EXAMINER	DOCUMENT NU	IMRER	_	DATE	COUNTRY	CLASS	SUBCLAS	SS TRANS	LATION		
NITIAL	DOCOMENTIA				000111111	OLAGO	00000	YES	NO		
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	JP 60-74643		04/	1985	Japan			ABST			

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FORM PTO-1449	U.S. DEPARTM PATENT AND	ATTY. DOCKET NO. ELM-2 Cont. 4		APPLICATION NO. 10/672,961			
	NFORMATION DISC	APPLICANT Glenn J. Leedy		CONFIRMATION NO. 9439			
,	STATEMENT BY APPLICANT					GROUP 2811	
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JP (JP 04-107964 04/1992 Japan					AB	ST
JP 402027600A 01/1990 Japan						AB	ST

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